## **EE210:** Analog Electronics

## **Question Set 7**

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1) Consider the circuit in Fig 1.  $\mu_n C_{ox} = 0.2mA/V^2$ ,  $I_0 = 1mA$ ,  $V_{DD} = 6V$ ,  $R_1 = R_2 = 2k\Omega$ ,  $V_{tn} = 1V$ .



Figure 1: Question 1.

a) Size M1 and M2 such that M1 is in saturation with a margin of 500 mV, and  $g_{M1} = 1$  mS.

**b**) Find the incremental resistances  $r_1$  and  $r_2$ .

c) Use the configuration to implement a common source amplifier.

**d**) If you want to implement a CCCS, where and how will you apply the i/p and take the o/p?

e) How is this config. different from a standard common gate config.?

f) If you want to implement a VCVS having gain  $\approx 1$  while driving a load  $R_L \approx 1 \mathrm{k}\Omega$  to  $2\mathrm{k}\Omega$ , what will you do?

2) The circuit shown in Fig. 2 is used to generate a bias voltage  $V_B = V_{tn} + V_{ov}$ . If we want to generate a bias voltage of  $V_B = V_{tn} + 2V_{ov}$ , how will you change the circuit without changing the  $I_0$ ?

3)  $I_0 = 1mA$ ,  $(W/L)_1 = 10$ ,  $\mu_n C_{ox} = 200\mu A/V^2$ ,  $\mu_p C_{ox} = 100\mu A/V^2$   $(W/L)_2 = 20$ ,  $V_{DD} = 5 V$ 







Figure 3: Question 3

a) Find the quiescent current through M1 and M2.

**b**) Between M1 and M2 ,what will you change to bias M1 at the edge of saturation region ?

c) Among the four types of biasing schemes that you have learnt, which one is being used here to bias M1?

- Observe the drain, feedback at source.
- Observe the drain, feedback at gate.
- Observe the source, feedback at source.
- Observe the drain, feedback at gate.

**d)** Find the maximum and minimum  $V_B$  required to keep both the transistors in saturation while maintaining the constraint of a minimum overdrive voltage of 100 mV?